



4-Pin DIP Phototransistor Optocouplers

FOD814, FOD817

Introduction or Description

The FOD814 consists of two gallium arsenide infrared emitting diodes, connected in inverse parallel, driving a silicon phototransistor output in a 4-pin dual in-line package. The FOD817 Series consists of a gallium arsenide infrared emitting diode driving a silicon phototransistor in a 4-pin dual in-line package.

Features

- AC Input Response (FOD814)
- Current Transfer Ratio in Selected Groups
 - ◆ FOD814: 20-300%
 - FOD814A: 50-150%
 - FOD817: 50-600%
 - FOD817A: 80-160%
 - ◆ FOD817B: 130–260%
 - FOD817C: 200-400%
 - FOD817D: 300-600%
- Minimum BV_{CEO} of 70 V Guaranteed
- Safety and Regulatory Approvals
 - ◆ UL1577, 5,000 VAC_{RMS} for 1 Minute
 - DIN EN/IEC60747-5-5
- This Device is Pb-Free

Typical Applications

- FOD814 Series
 - AC Line Monitor
 - Unknown Polarity DC Sensor
 - Telephone Line Interface
- FOD817 Series
 - Power Supply Regulators
 - Digital Logic Inputs
 - Microprocessor Inputs





PDIP4 GW CASE 709AH

MARKING DIAGRAM



V = VDE Mark

X = One Digit Year Code
ZZ = Two Digit Work Week
Y = Assembly Package Code

\$Y = Logo

81x = Specific Device Code

x = 4 or 7

ORDERING INFORMATION

See detailed ordering and shipping information on page 8 of this data sheet.

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FUNCTIONAL BLOCK DIAGRAM

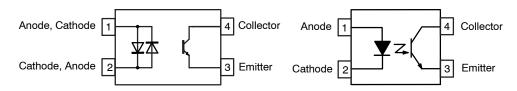


Figure 1. Schematic - FOD814

Figure 2. Schematic - FOD817

SAFETY AND INSULATION RATINGS

Parameter		Characteristics
Installation Classifications per DIN VDE	< 150 V _{RMS}	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V _{RMS}	I–III
Climatic Classification	30/110/21	
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V _{PR}	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	1360	V _{peak}
	Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with $t_m = 1 \text{ s}$, Partial Discharge < 5 pC	1594	
V _{IORM}	Maximum Working Insulation Voltage	850	
V _{IOTM}	Highest Allowable Over-Voltage	8000	
	External Creepage	≥7	mm
	External Clearance	≥7	
	External Clearance (for Option W, 0.4" Lead Spacing)	≥ 10	
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	
T _S	Case Temperature (Note 1)	175	°C
I _{S,INPUT}	Input Current (Note 1)	400	mA
P _{S,OUTPUT}	Output Power (Note 1)	700	mW
R _{IO}	Insulation Resistance at T _S , V _{IO} = 500 V (Note 1)	> 10 ¹¹	Ω

As per DIN EN/IEC 60747–5–5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

ABSOLUTE MAXIMUM RATINGS $T_A = 25^{\circ}C$ unless otherwise specified.

		Value		
Symbol	Parameter	FOD814	FOD817	Unit
TOTAL DEV	CE			
T _{STG}	Storage Temperature	-55 to +150		°C
T _{OPR}	Operating Temperature	-55 to +105	-55 to +110	
TJ	Junction Temperature	-55 to +125		
T _{SOL}	Lead Solder Temperature	260 for 10 s		
θЈС	Junction-to-Case Thermal Resistance	210		°C/W
P _{TOT}	Total Device Power Dissipation	20	00	mW

^{1.} Safety limit values - maximum values allowed in the event of a failure.

ABSOLUTE MAXIMUM RATINGS T_A = 25°C unless otherwise specified. (continued)

		Va		
Symbol	Parameter	FOD814	FOD817	Unit
EMITTER	•		-	
l _F	Continuous Forward Current	±50	50	mA
V_{R}	Reverse Voltage		6	V
P_{D}	Power Dissipation	7	70	
	Derate Above 100°C	1	1.7	
DETECTOR				
V_{CEO}	Collector-Emitter Voltage	7	70	V
V _{ECO}	Emitter-Collector Voltage		6	
I _C	Continuous Collector Current	Ę	50	
P _C	Collector Power Dissipation	1	50	mW
	Derate Above 90°C	2	2.9	mW/°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTICS $T_A = 25^{\circ}C$ unless otherwise specified.

INDIVIDUAL COMPONENT CHARACTERISTICS

Symbol	Parameter	Device	Test Conditions	Min	Тур	Max	Unit
Emmiter				-			
V _F	Forward Voltage	FOD814	I _F = ±20 mA	_	1.2	1.4	V
		FOD817	I _F = 20 mA	-	1.2	1.4	
I _R	Reverse Current	FOD817	V _R = 4.0 V	-	-	10	μΑ
Ct	Terminal Capacitance	FOD814	V = 0, f = 1 kHz	-	50	250	pF
		FOD817		-	30	250	
Detector							
I _{CEO}	Collector Dark Current	FOD814	V _{CE} = 20 V, I _F = 0	-	-	100	nA
		FOD817		_	-	100	
BV _{CEO}	Collector-Emitter Breakdown	FOD814	$I_C = 0.1 \text{ mA}, I_F = 0$	70	-	-	V
	Voltage	FOD817		70	-	-	
BV _{ECO}	Emitter-Collector Breakdown Voltage	FOD814	$I_E = 10 \mu A, I_F = 0$	6	-	-	
		-					I

DC TRANSFER CHARACTERISTICS

Symbol	Parameter	Device	Test Conditions	Min	Тур	Max	Unit
CTR	Current Transfer Ratio (Note 2)	FOD814	$I_F = \pm 1$ mA, $V_{CE} = 5$ V	20	_	300	%
		FOD814A		50	_	150	
		FOD817	I _F = 5 mA, V _{CE} = 5 V	50	_	600	
		FOD817A		80	_	160	
		FOD817B		130	_	260	
		FOD817C		200	_	400	
		FOD817D		300	_	600	
V _{CE(SAT)}	Collector-Emitter Saturation	FOD814	$I_F = \pm 20 \text{ mA}, I_C = 1 \text{ mA}$	-	0.1	0.2	V
	Voltage	FOD817	$I_F = 20 \text{ mA}, I_C = 1 \text{ mA}$	-	0.1	0.2	

ELECTRICAL CHARACTERISTICS T_A = 25°C unless otherwise specified. (continued)

AC TRANSFER CHARACTERISTICS

Symbol	Parameter	Device	Test Conditions	Min	Тур	Max	Unit
f _C	Cut-Off Frequency	FOD814	$V_{CE} = 5 \text{ V, } I_{C} = 2 \text{ mA,}$ $R_{L} = 100 \Omega, -3 \text{ dB}$	15	80	-	kHz
t _r	Response Time (Rise)	FOD814, FOD817	V _{CE} = 2 V, I _C = 2 mA,	-	4	18	μs
t _f	Response Time (Fall)	FOD814, FOD817	R_L = 100 Ω (Note 3)	_	3	18	

ISOLATION CHARACTERISTICS

Symbol	Parameter	Device	Test Conditions	Min	Тур	Max	Unit
V _{ISO}	Input-Output Isolation Voltage (Note 4)	FOD814, FOD817	$f = 60 \text{ Hz}, t = 1 \text{ min}, \\ I_{I-O} \le 2 \mu A$	5000	-	-	VAC _{RMS}
R _{ISO}	Isolation Resistance	FOD814, FOD817	V _{I-O} = 500 V _{DC}	5x10 ¹⁰	1x10 ¹¹	-	Ω
C _{ISO}	Isolation Capacitance	FOD814, FOD817	V _{I-O} = 0, f = 1 MHz	-	0.6	1.0	pf

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 2. Current Transfer Ratio (CTR) = I_C / I_F x 100%
- 3. For test circuit setup and waveforms, refer to page 5.
- 4. For this test, Pins 1 and 2 are common, and Pins 3 and 4 are common.

TYPICAL ELECTRICAL/OPTICAL CHARACTERISTICS CURVES

 $T_A = 25^{\circ}C$ unless otherwise specified.

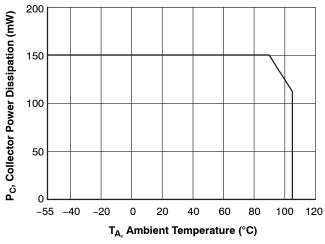


Figure 3. Collector Power Dissipation vs.
Ambient Temperature (FOD814)

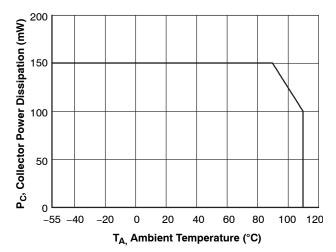


Figure 4. Collector Power Dissipation vs.
Ambient Temperature (FOD817)

TYPICAL ELECTRICAL/OPTICAL CHARACTERISTICS CURVES

 $T_A = 25^{\circ}C$ unless otherwise specified. (continued)

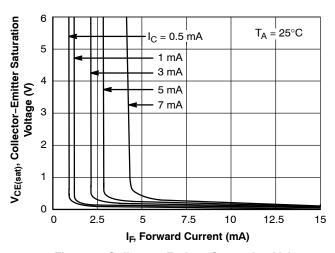


Figure 5. Collector-Emitter Saturation Voltage vs. Forward Current

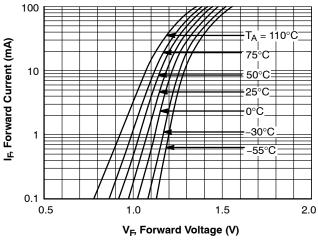


Figure 7. Forward Current vs. Forward Voltage (FOD817)

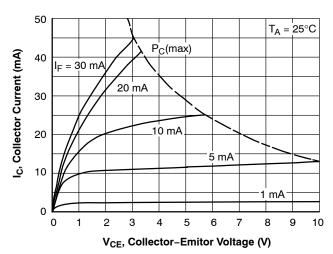


Figure 9. Collector Current vs. Collector-Emitor Voltage (FOD814)

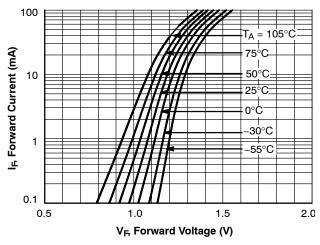


Figure 6. Forward Current vs. Forward Voltage (FOD814)

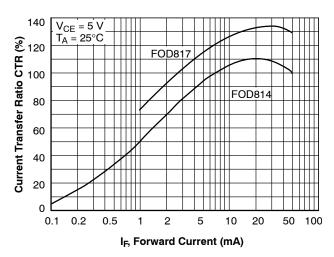


Figure 8. Current Transfer Ratio vs. Forward Current

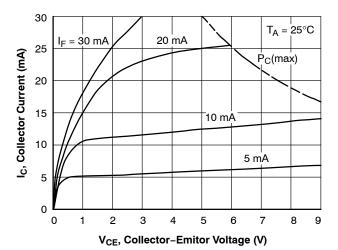


Figure 10. Collector Current vs. Collector-Emitor Voltage (FOD817)

TYPICAL ELECTRICAL/OPTICAL CHARACTERISTICS CURVES

 $T_A = 25^{\circ}C$ unless otherwise specified. (continued)

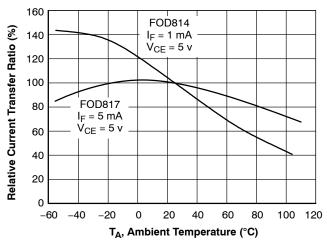


Figure 11. Relative Current Transfer Ratio vs.

Ambient Temperature

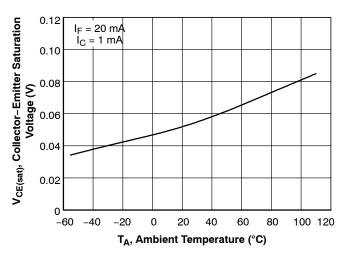


Figure 12. Collector-Emitter Saturation Voltage vs. Ambient Temperature

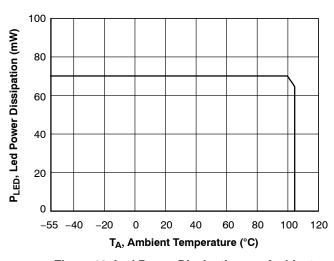


Figure 13. Led Power Dissipation vs. Ambient Temperature (FOD814)

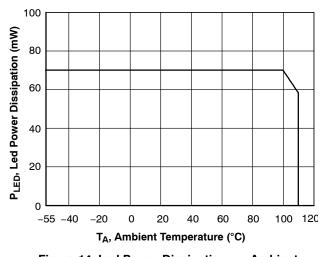


Figure 14. Led Power Dissipation vs. Ambient Temperature (FOD817)

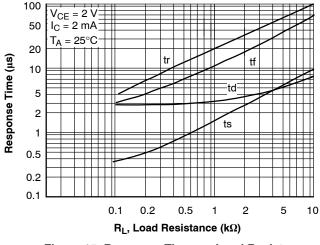


Figure 15. Response Time vs. Load Resistance

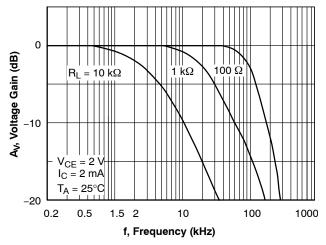


Figure 16. Frequency Response

TYPICAL ELECTRICAL/OPTICAL CHARACTERISTICS CURVES

 $T_A = 25^{\circ}C$ unless otherwise specified. (continued)

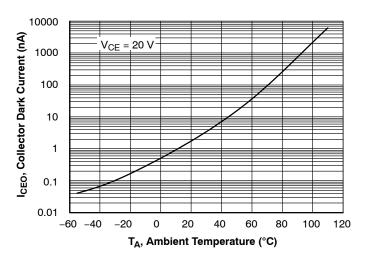


Figure 17. Collector Dark Current vs. Ambient Temperature

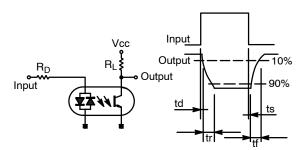


Figure 18. Test Circuit for Response Time

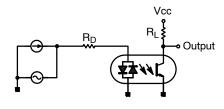


Figure 19. Test Circuit for Frequency Response

REFLOW PROFILE

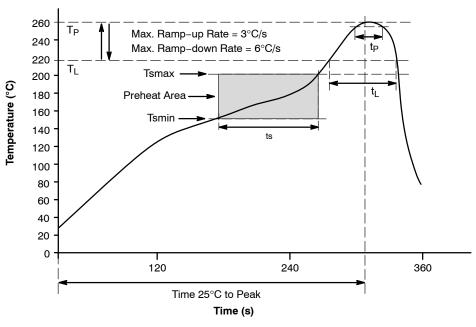


Figure 20. Reflow Profile

REFLOW PROFILE

Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (t _S) from (Tsmin to Tsmax)	60–120 s
Ramp-up Rate (t _L to t _P)	3°C/s max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60–150 s
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of 260°C	30 s
Ramp-down Rate (T _P to T _L)	6°C/s max.
Time 25°C to Peak Temperature	8 min max.

ORDERING INFORMATION

Part Number	Package	Shipping [†]
FOD817X	DIP 4-Pin	Tube (100 units per tube)
FOD817XS	SMT 4-Pin (Lead Bend)	Tube (100 units per tube)
FOD817XSD	SMT 4-Pin (Lead Bend)	Tape and Reel (1,000 units per reel)
FOD817X300	DIP 4-Pin, DIN EN/IEC60747-5-5 option	Tube (100 units per tube)
FOD817X3S	SMT 4-Pin (Lead Bend), DIN EN/IEC60747-5-5 option	Tube (100 units per tube)
FOD817X3SD	SMT 4-Pin (Lead Bend), DIN EN/IEC60747-5-5 option	Tape and Reel (1,000 units per reel)
FOD817X300W	DIP 4-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 option	Tube (100 units per tube)

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

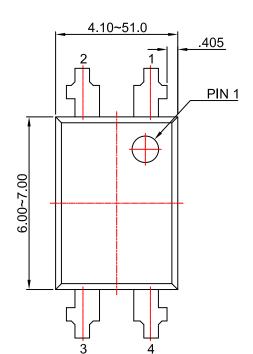
NOTE: The product orderable part number system listed in this table also applies to the FOD814 products. "X" denotes the Current Transfer Ratio (CTR) options.





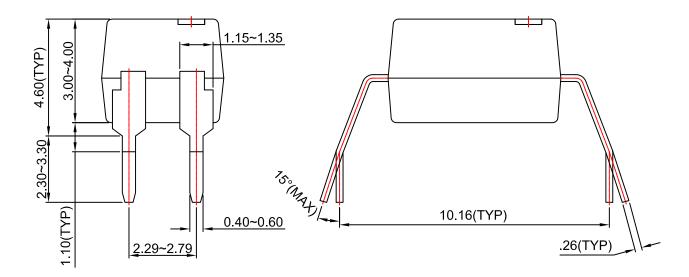
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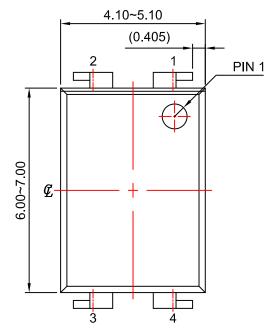
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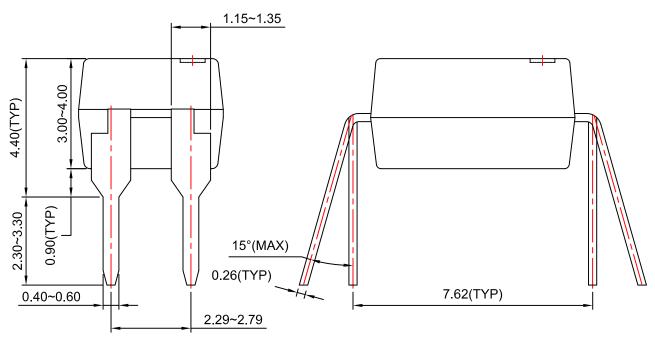
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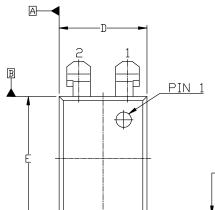
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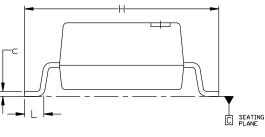
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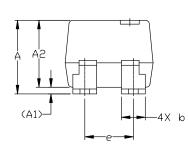


ISSUE B

NOTES:

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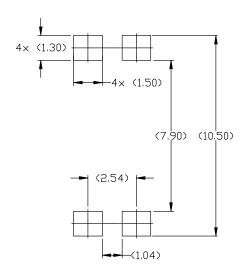




TOP VIEW

END VIEW

SIDE VIEW



	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
А	3.85 (TYP)			
A1	0.35 (REF)			
A2	3.00	3.50	4.00	
b	1.15	1.25	1.35	
С	0.26 (REF)			
D	4.10	4.60	5.10	
E	6.00	6.50	7.00	
е	2.29	2.54	2.79	
Н	9.86	10.16	10.46	
L	0.75		1.25	

LAND PATTERN RECOMMENDATION

For additional information on our Pb-Free strategy and soldering details, please download the IIN Semiconductor Soldering and Mounting Techniques Reference Manual, SILDERRM/D.

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